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Hsiao et al.

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(54) **EMBEDDED PASSIVE CHIP DEVICE AND METHOD OF MAKING THE SAME**

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(22) Filed: **Oct. 2, 2017**

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(30) **Foreign Application Priority Data**

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H01L 21/768 (2006.01)
H01L 21/78 (2006.01)
H01F 41/04 (2006.01)

(Continued)

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CPC **H01L 28/10** (2013.01); **H01F 17/0006** (2013.01); **H01F 41/04** (2013.01); **H01F 41/046** (2013.01); **H01L 21/76873** (2013.01);

H01L 21/78 (2013.01); **H01L 23/645** (2013.01); **H01F 2017/0066** (2013.01)

(58) **Field of Classification Search**

CPC H01L 28/10; H01L 21/76871
USPC 257/531; 438/467
See application file for complete search history.

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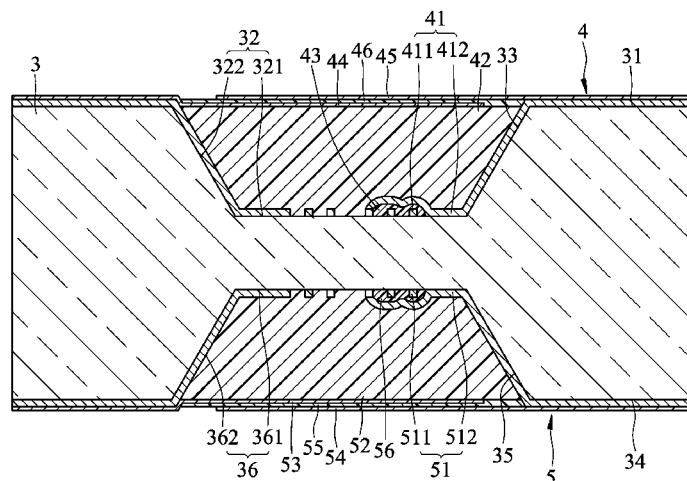
Primary Examiner — Jami Valentine Miller

(74) Attorney, Agent, or Firm — Womble Bond Dickinson (US) LLP

(57) **ABSTRACT**

An embedded passive chip device includes a chip body and a functional layered structure. The chip body has a circuit-forming surface that is formed with a recess. The functional layered structure is formed on the chip body and includes a conductive layer that has at least a portion which covers at least partially the circuit-forming surface, and a magnetic layer that is disposed within the recess and that is inductively coupled to the conductive layer for generating inductance. A method of making the embedded passive chip device is also disclosed.

6 Claims, 32 Drawing Sheets



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H01L 23/64 (2006.01)
H01F 17/00 (2006.01)

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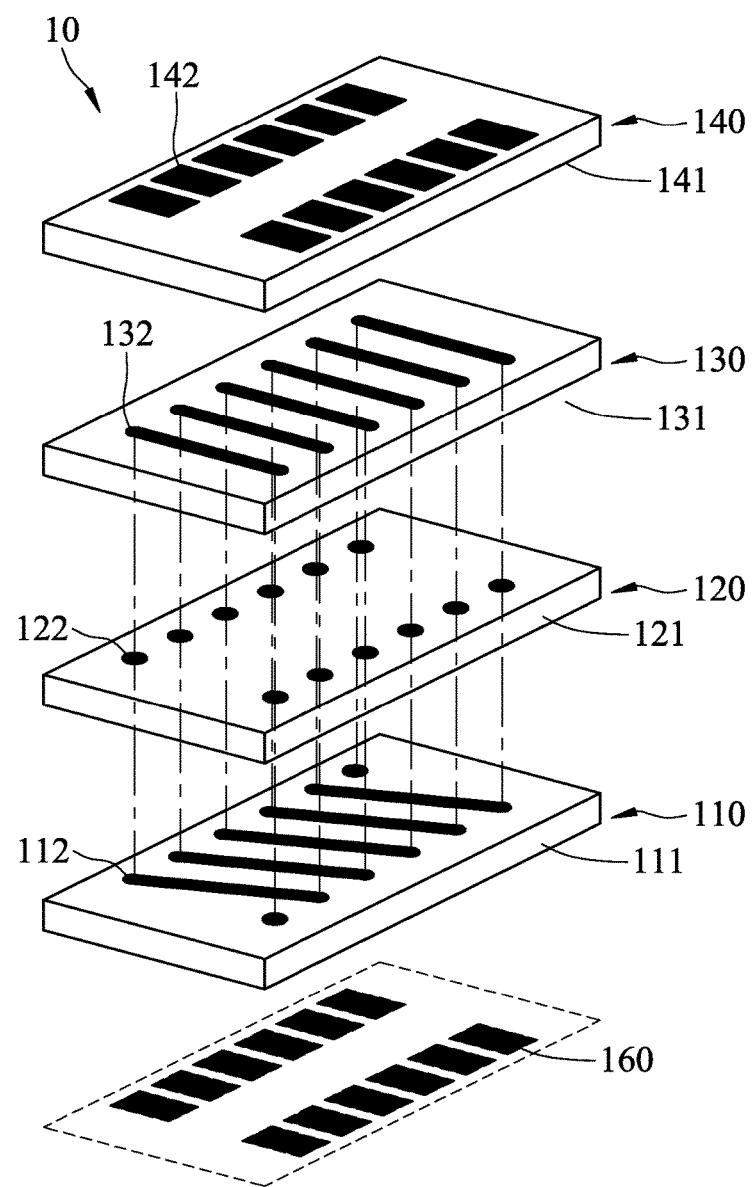


FIG.1
PRIOR ART

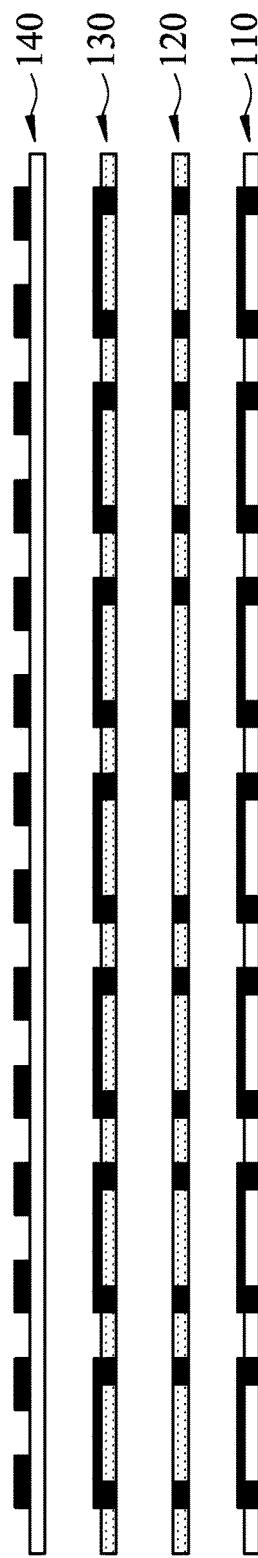


FIG.2A
PRIOR ART

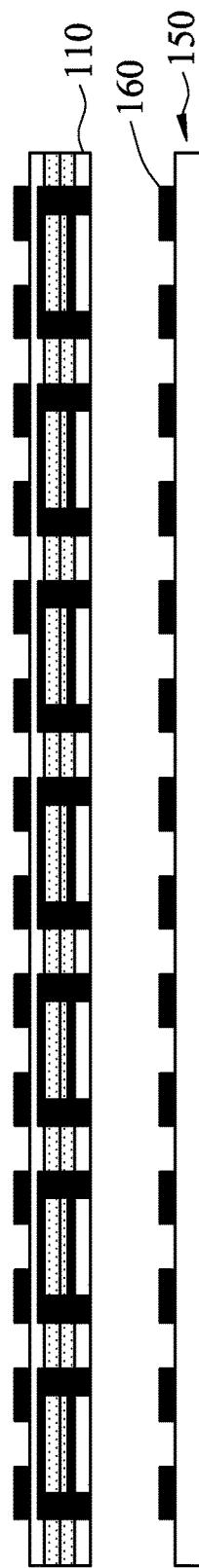


FIG.2B
PRIOR ART

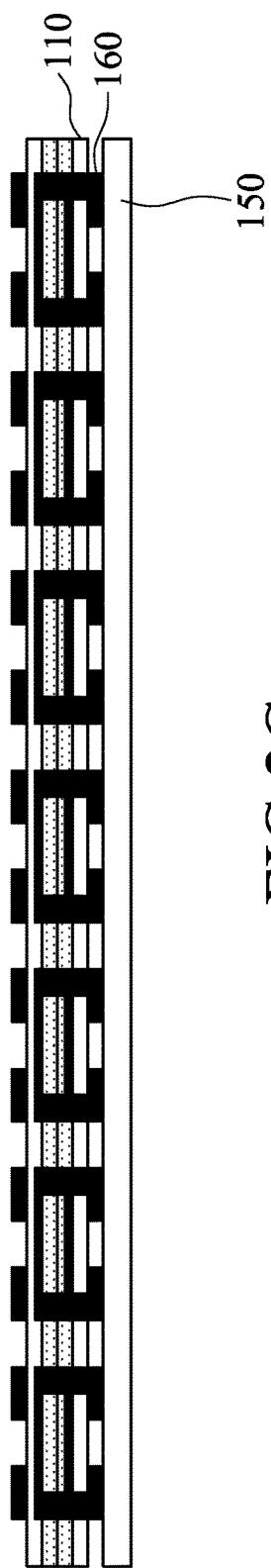


FIG. 2C
PRIOR ART

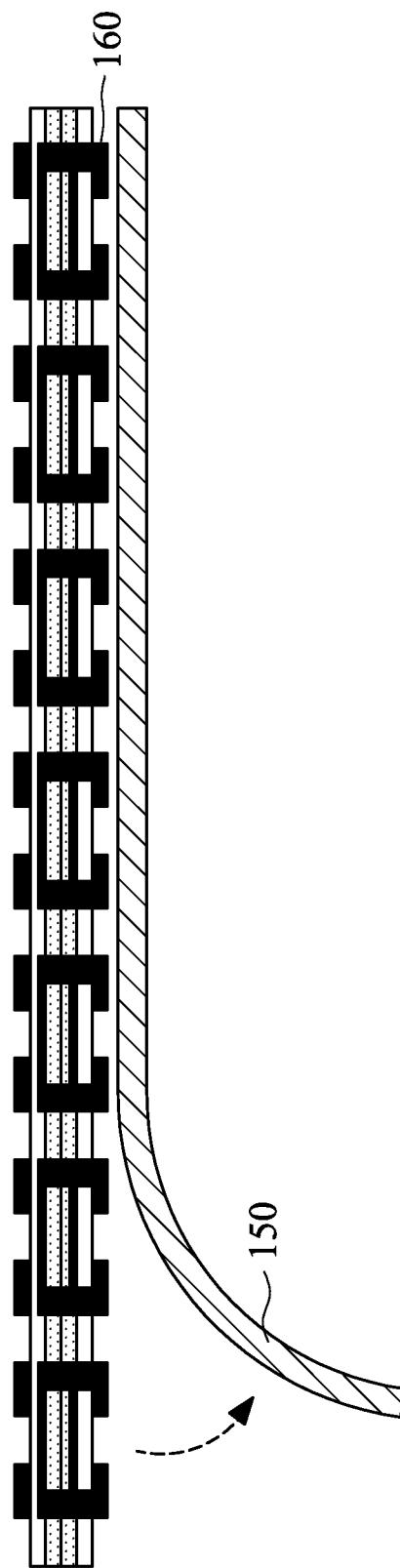


FIG.2D
PRIOR ART

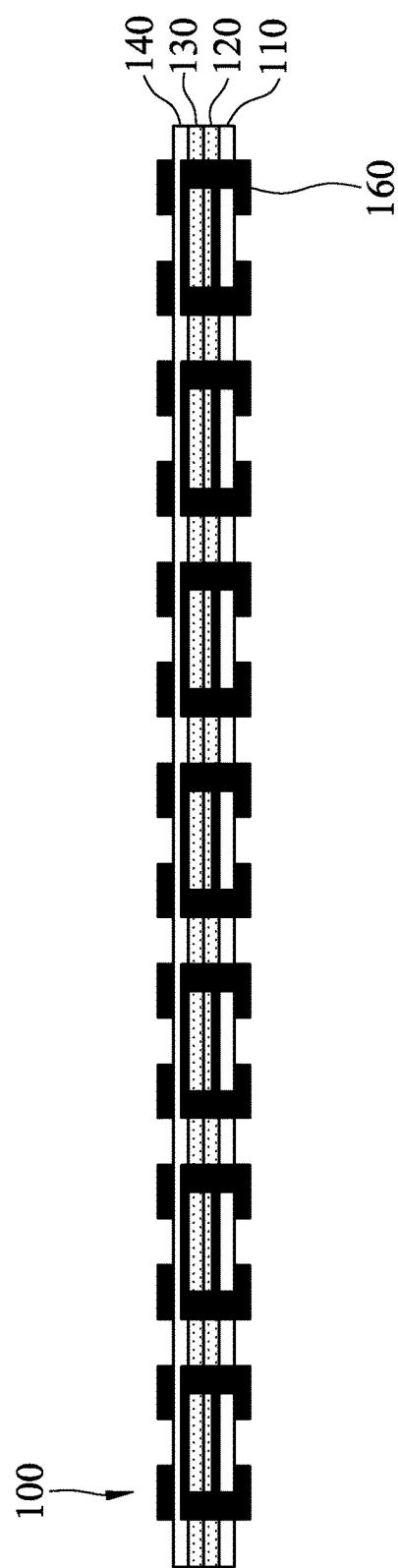


FIG.2E
PRIOR ART

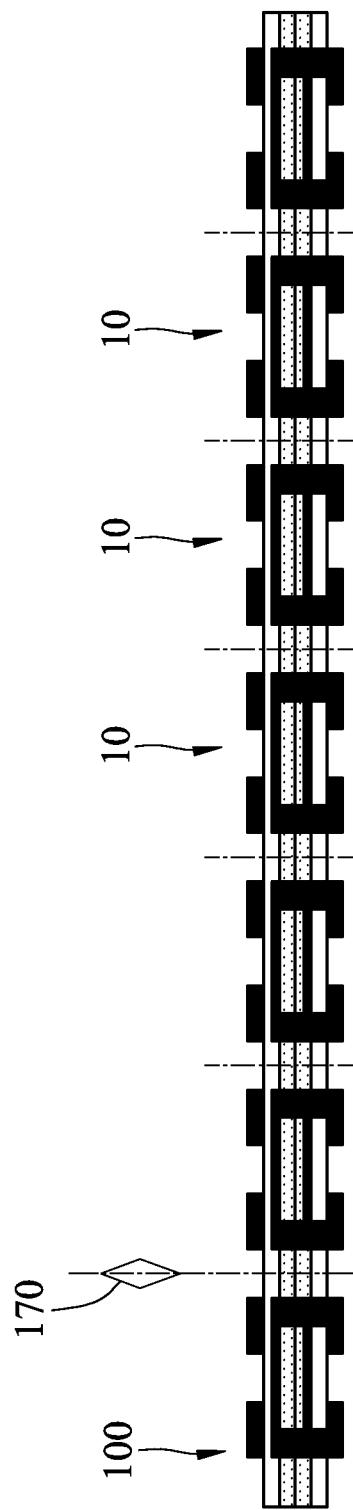


FIG.2F
PRIOR ART

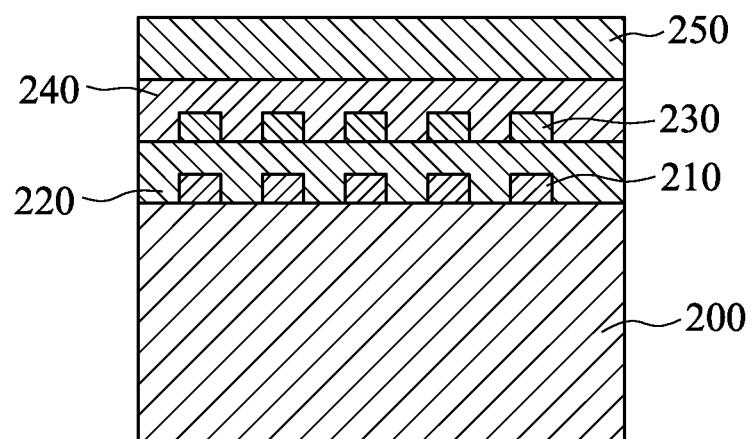


FIG.3
PRIOR ART

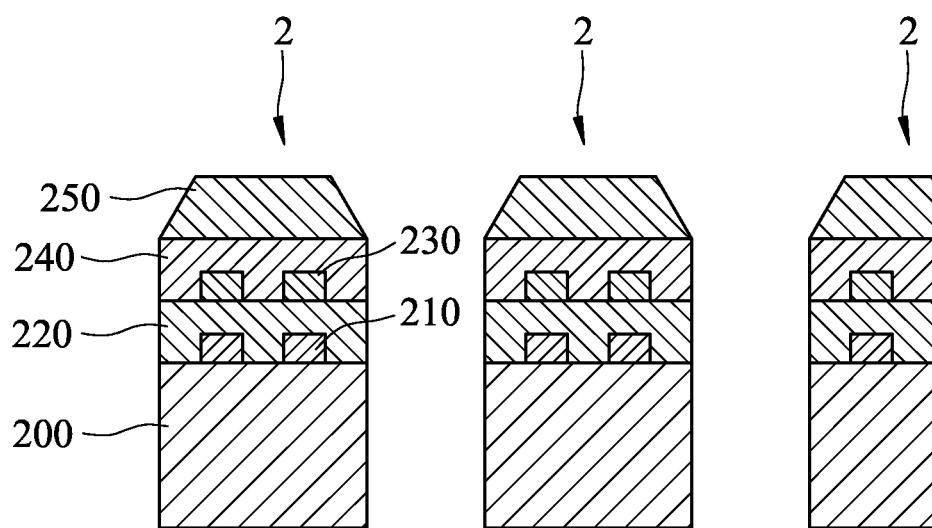


FIG.4
PRIOR ART

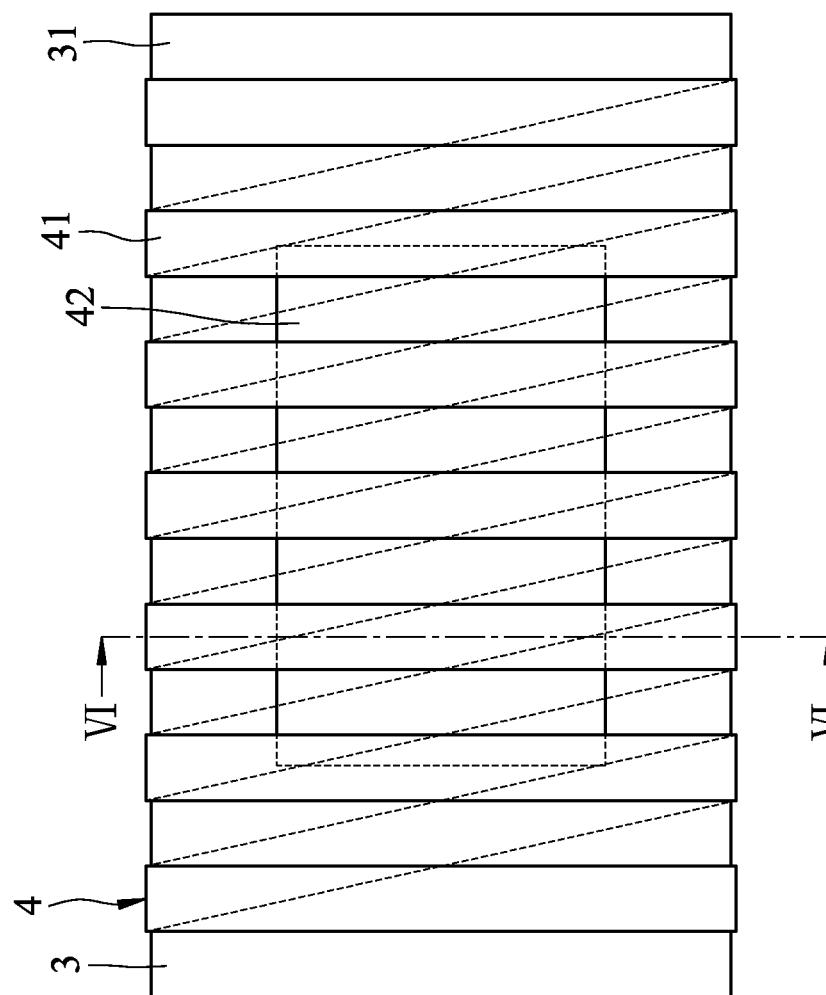


FIG.5

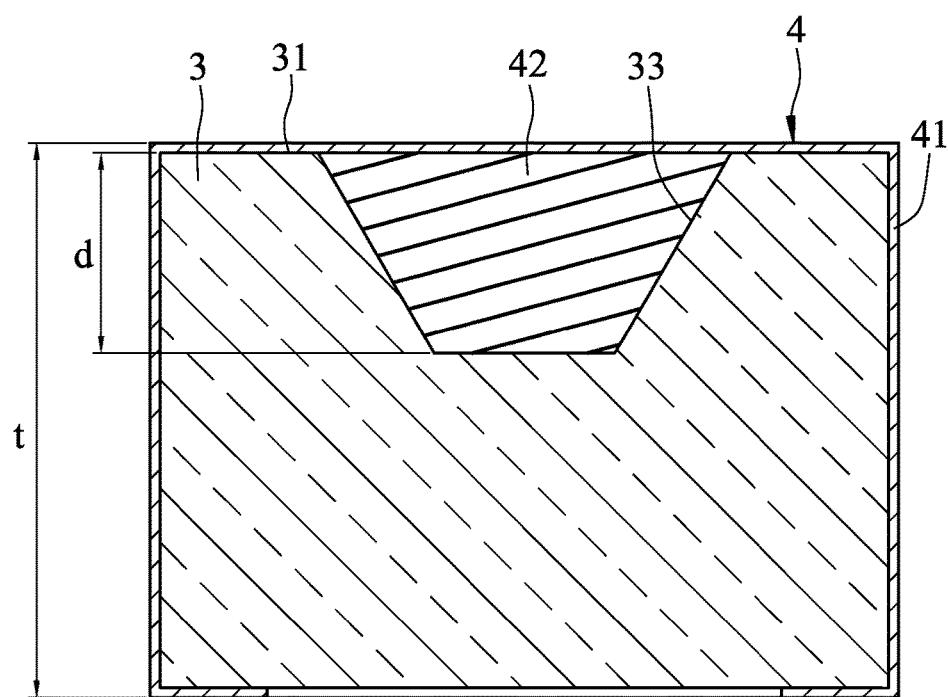


FIG.6

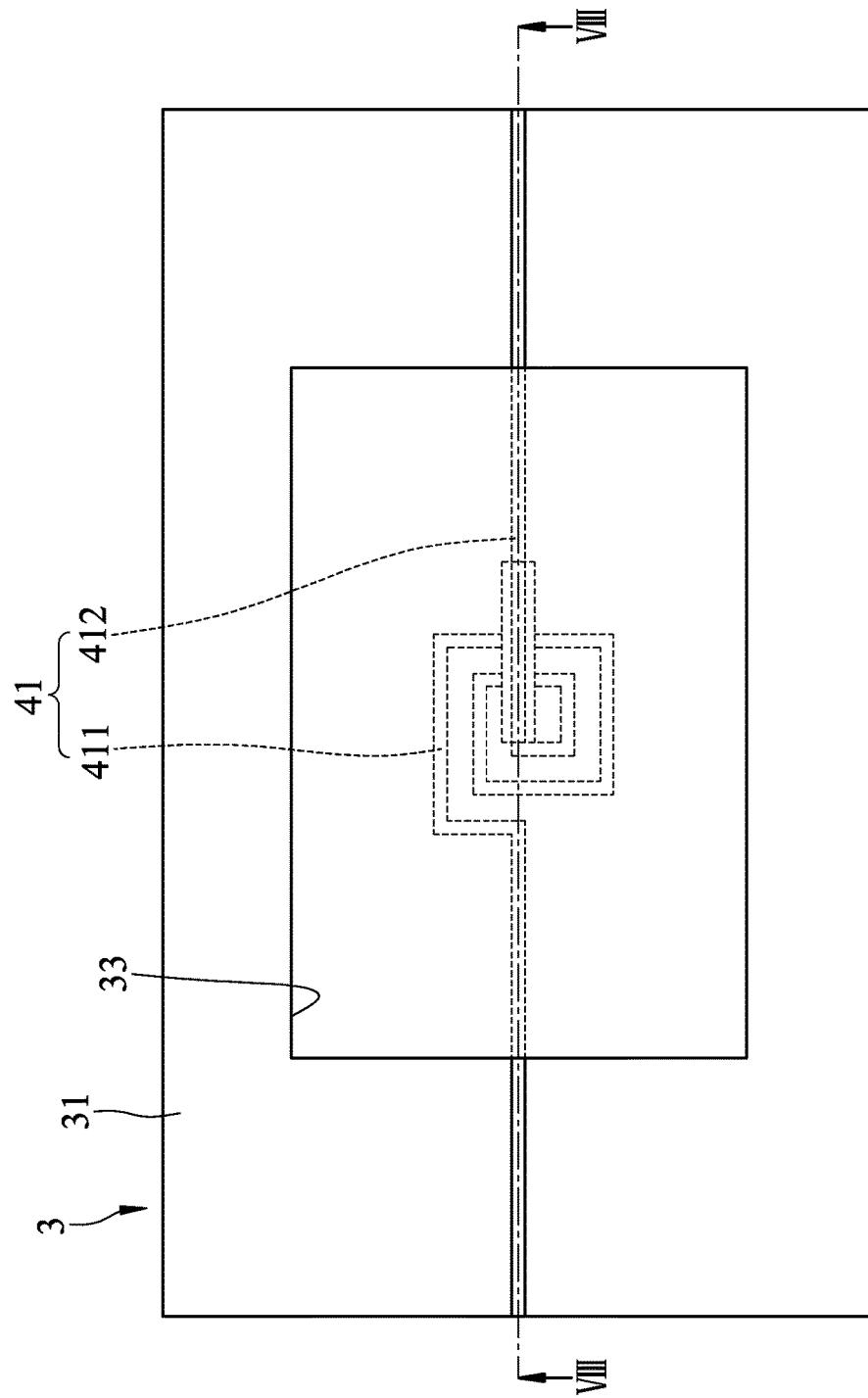


FIG.7

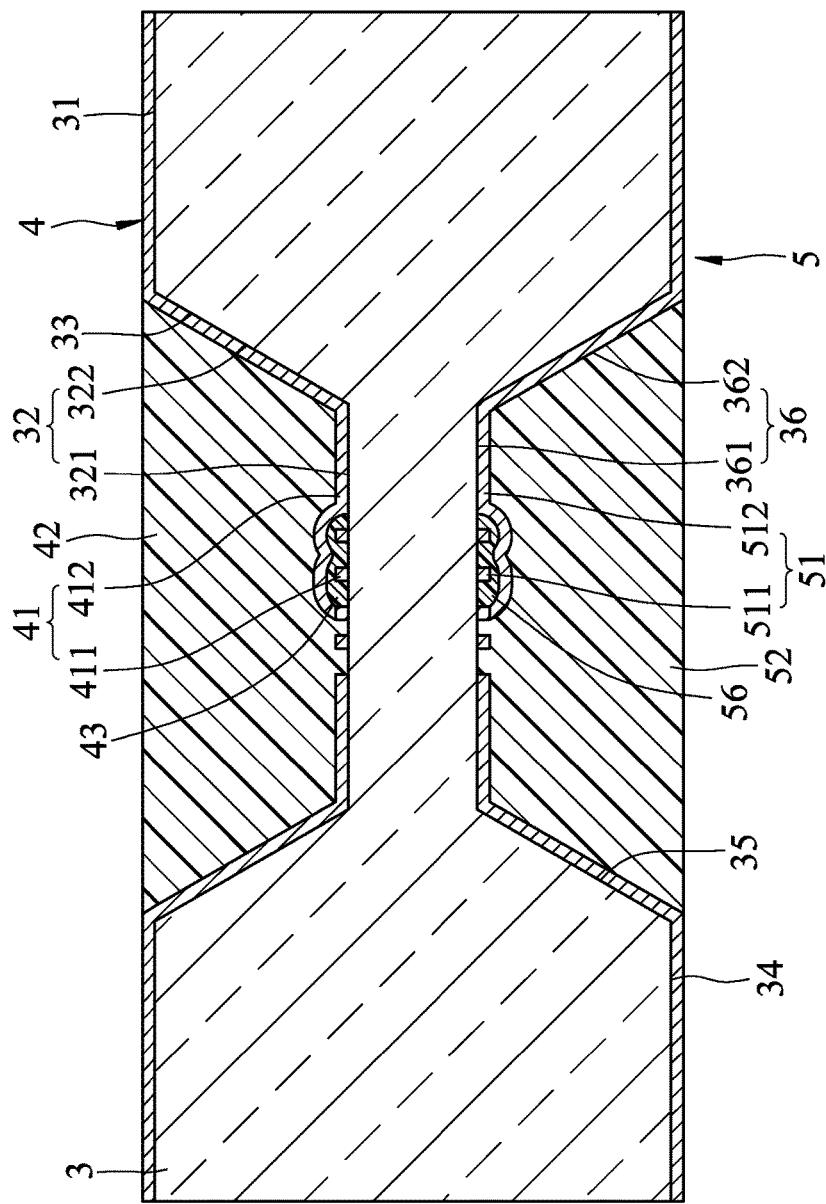


FIG.8

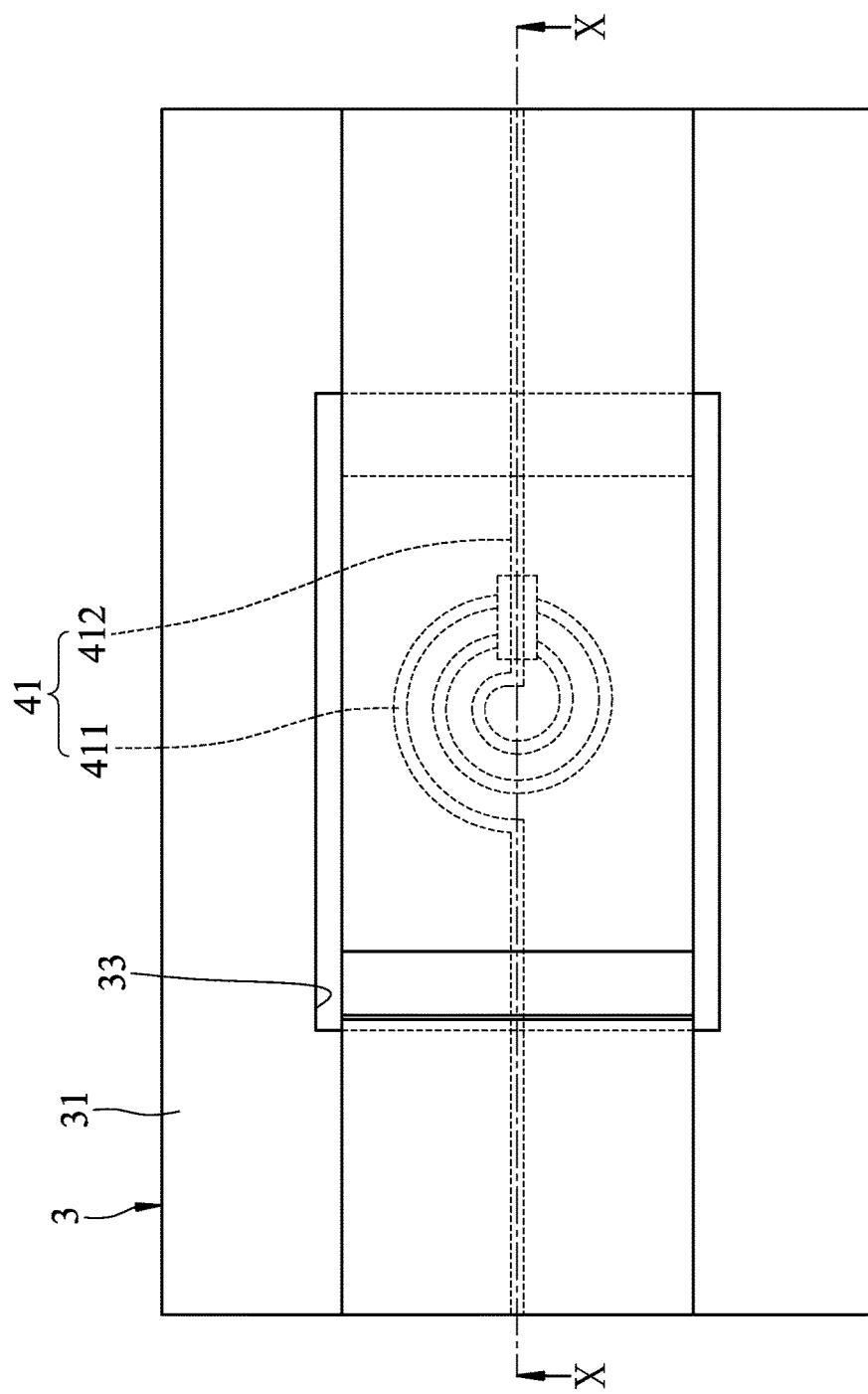


FIG.9

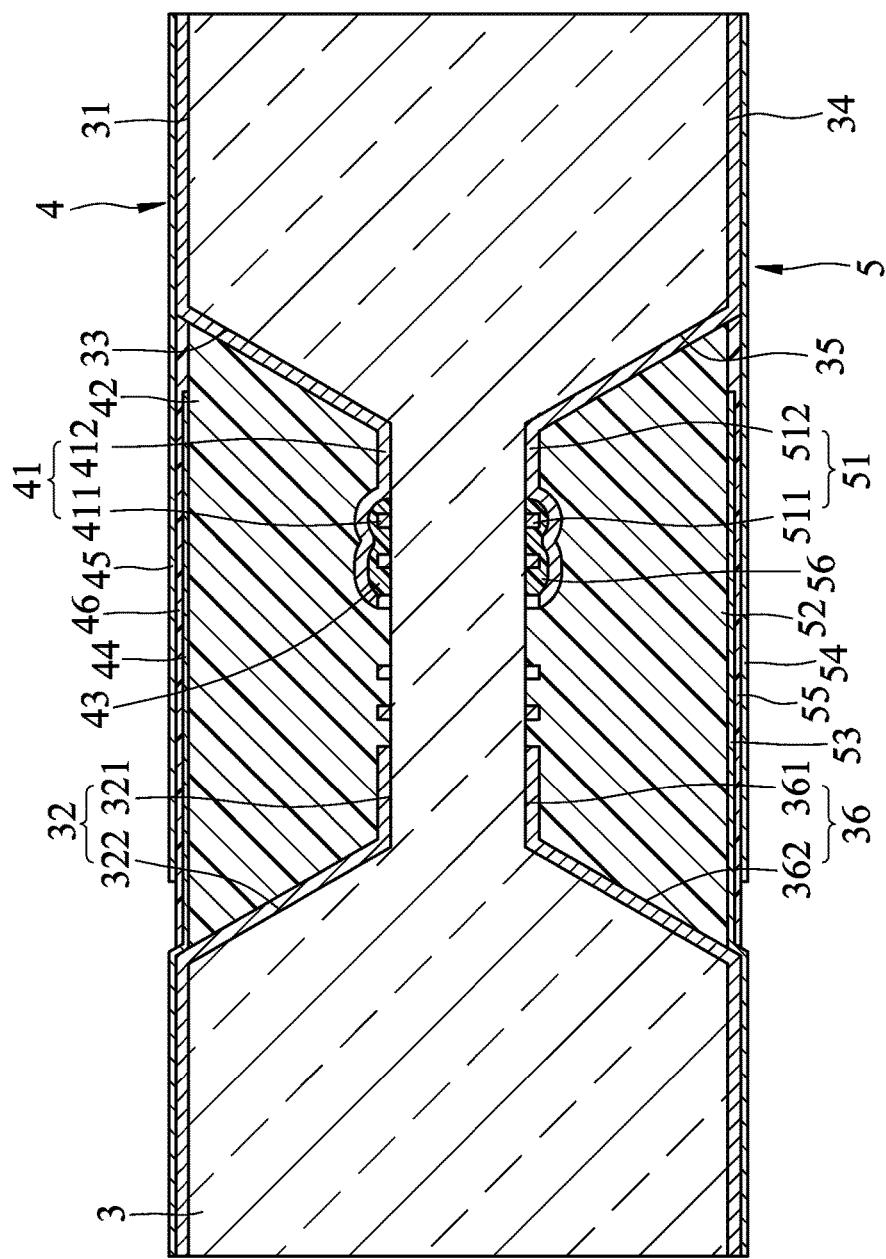


FIG. 10

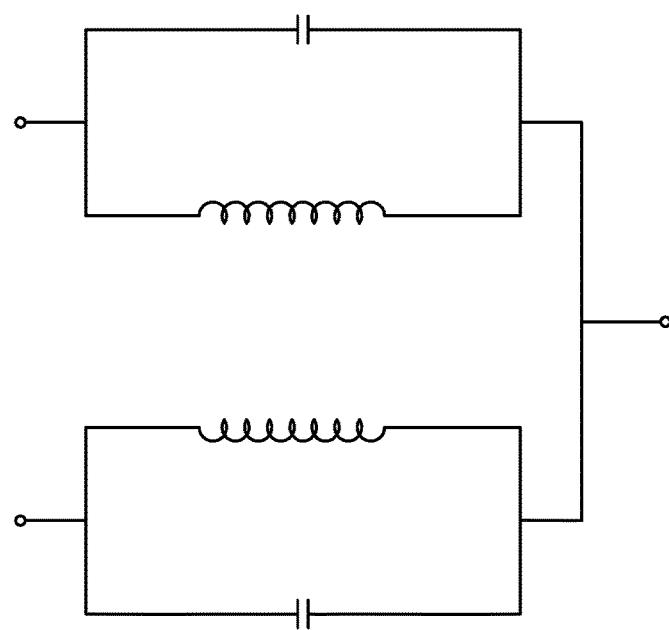


FIG.11

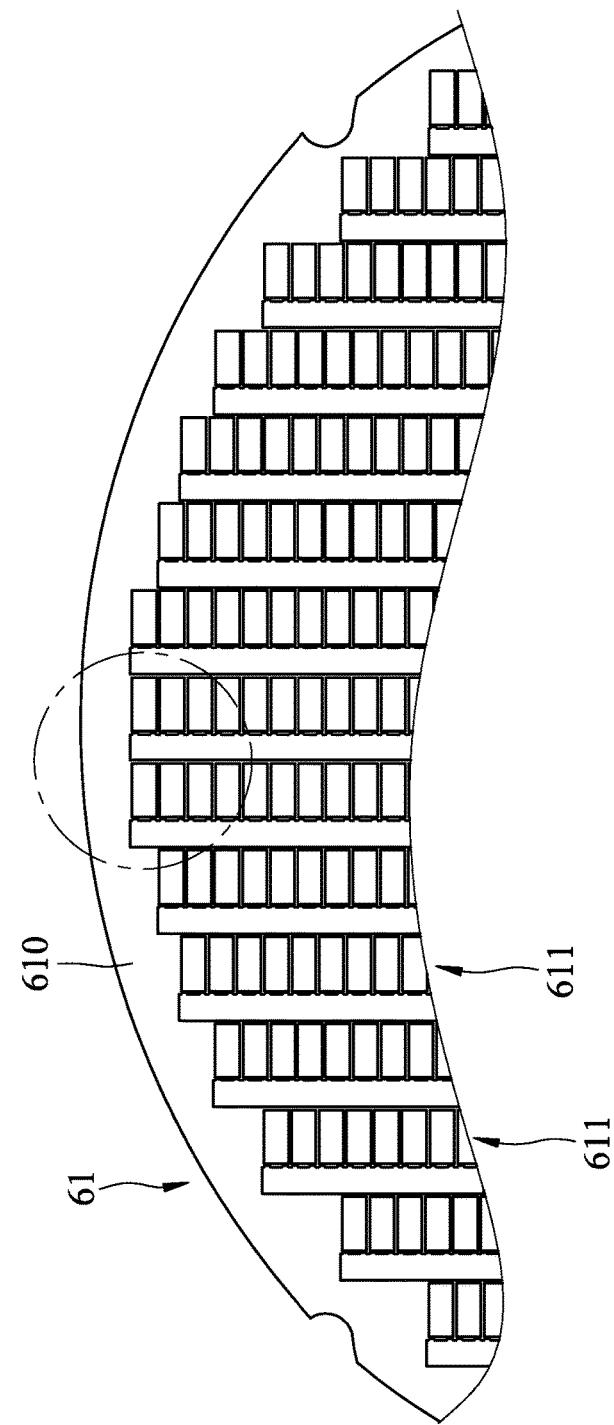
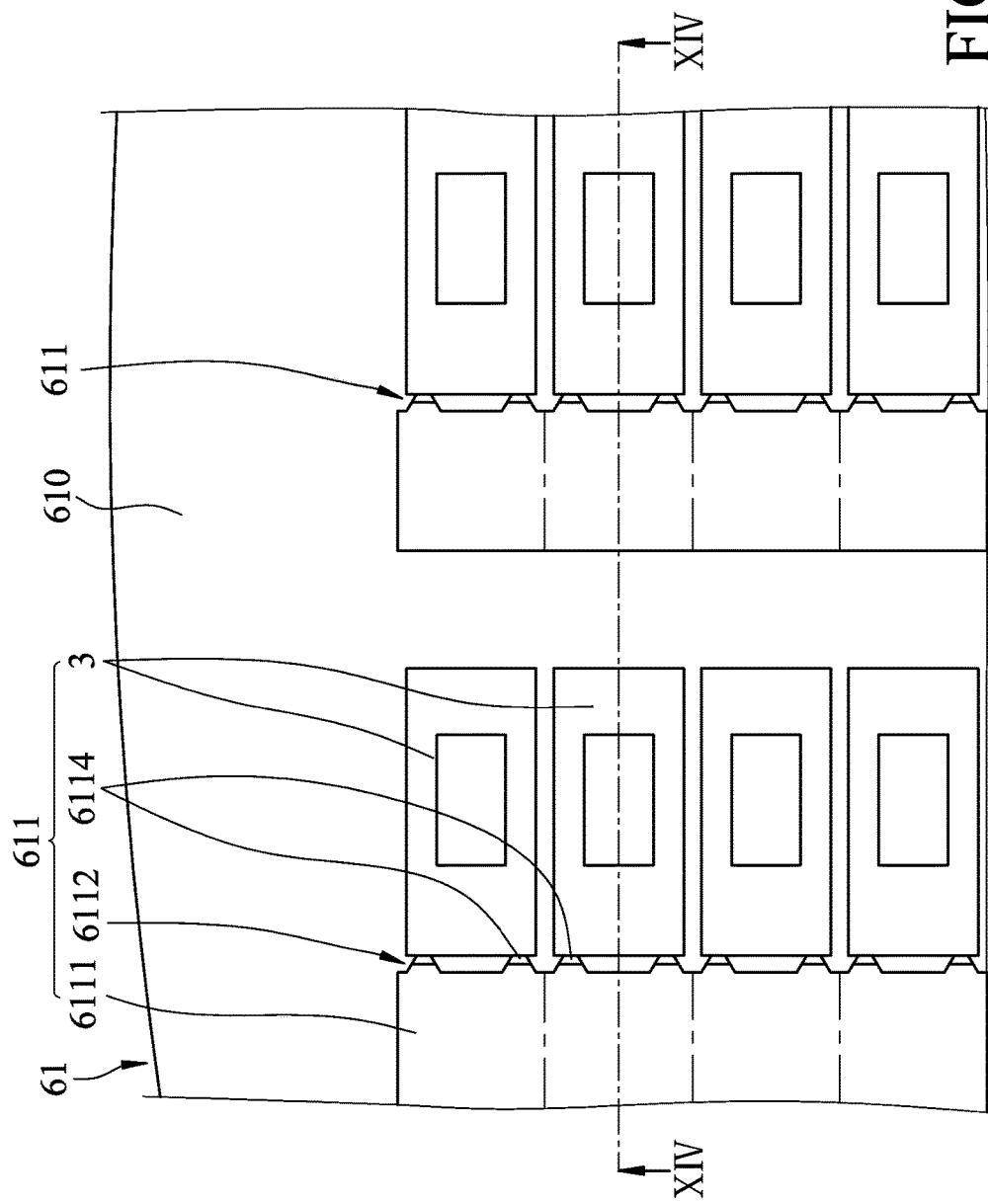


FIG.13



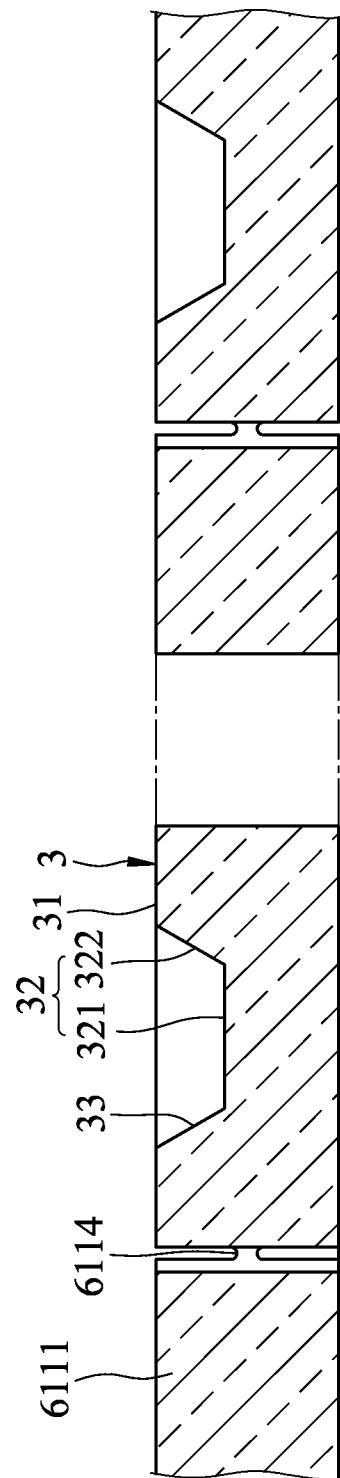


FIG.14

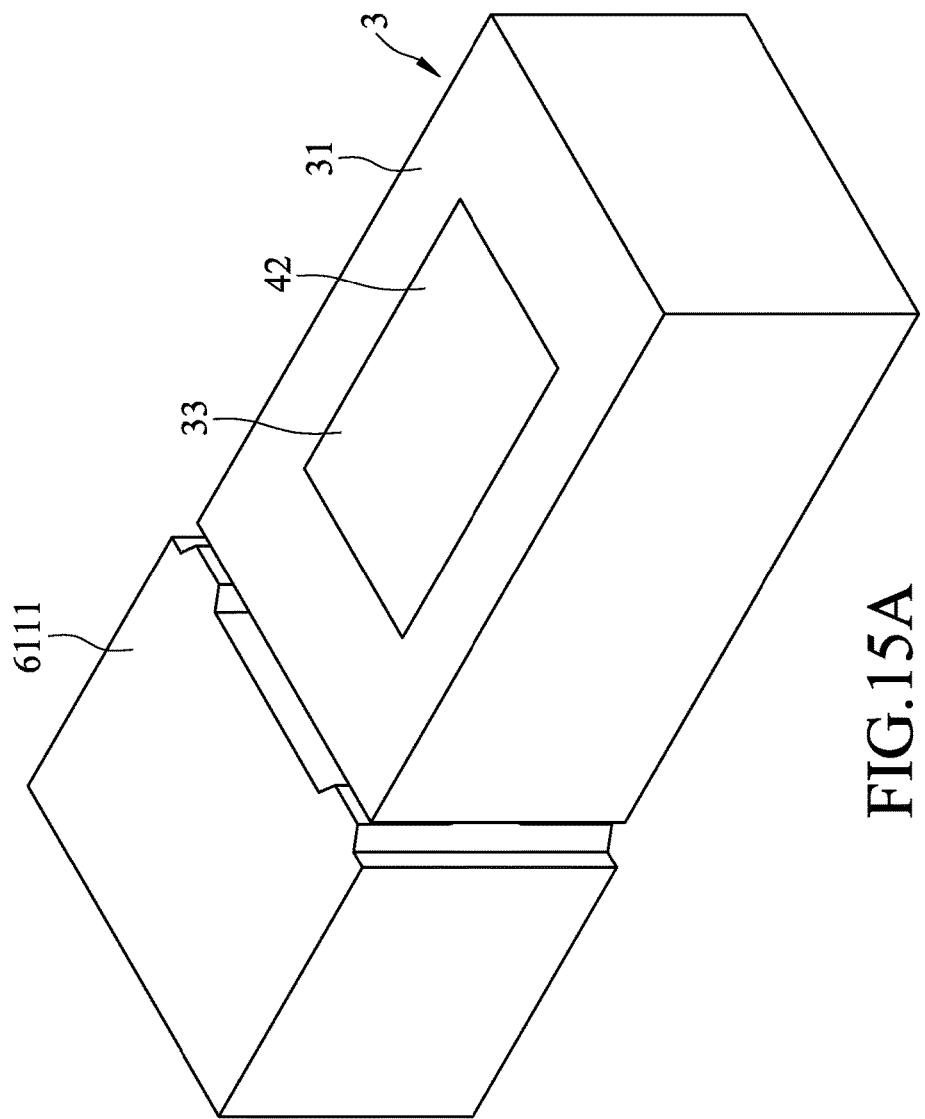


FIG. 15A

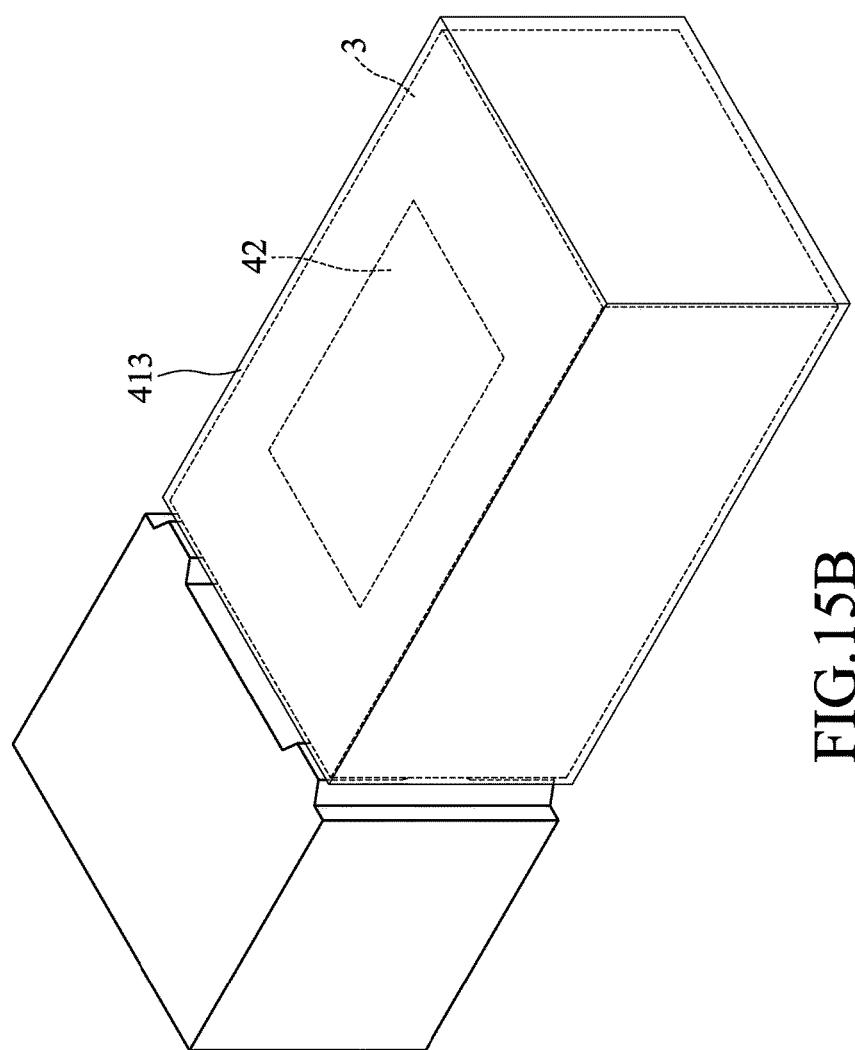


FIG.15B

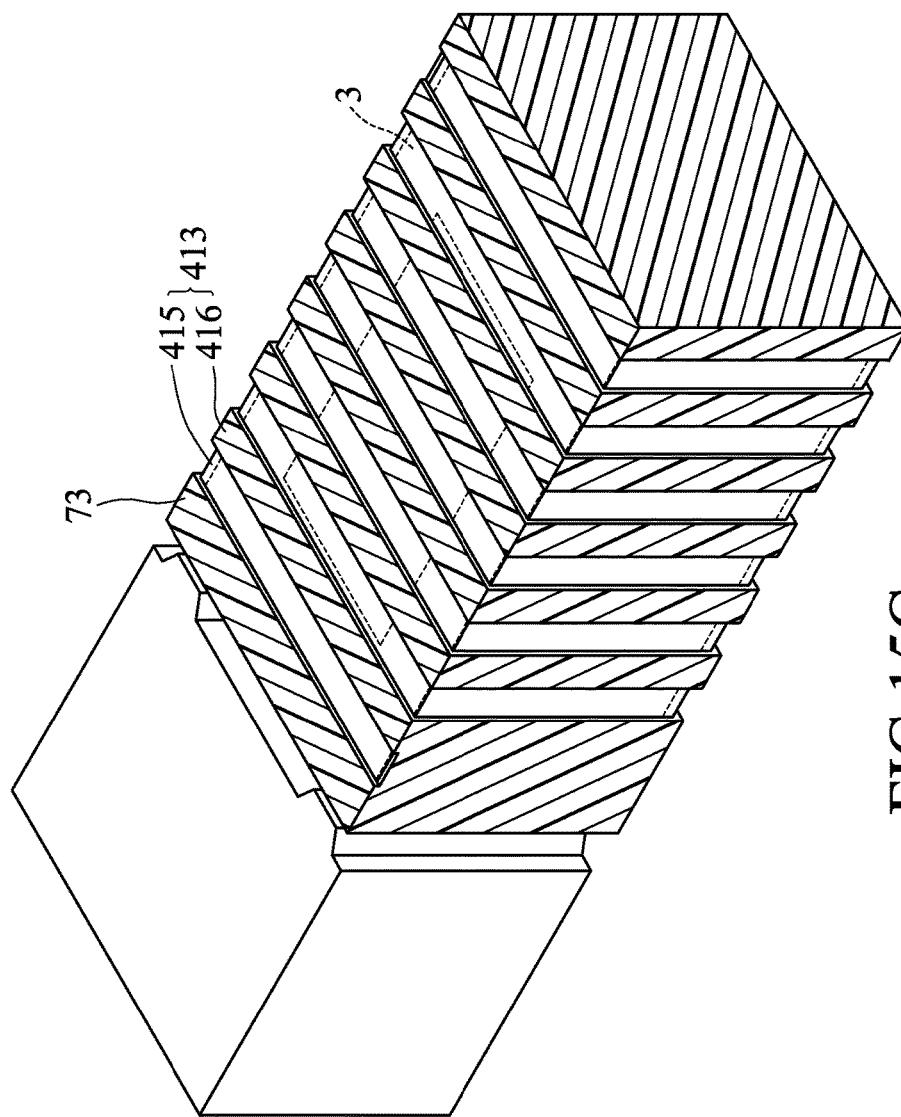


FIG. 15C

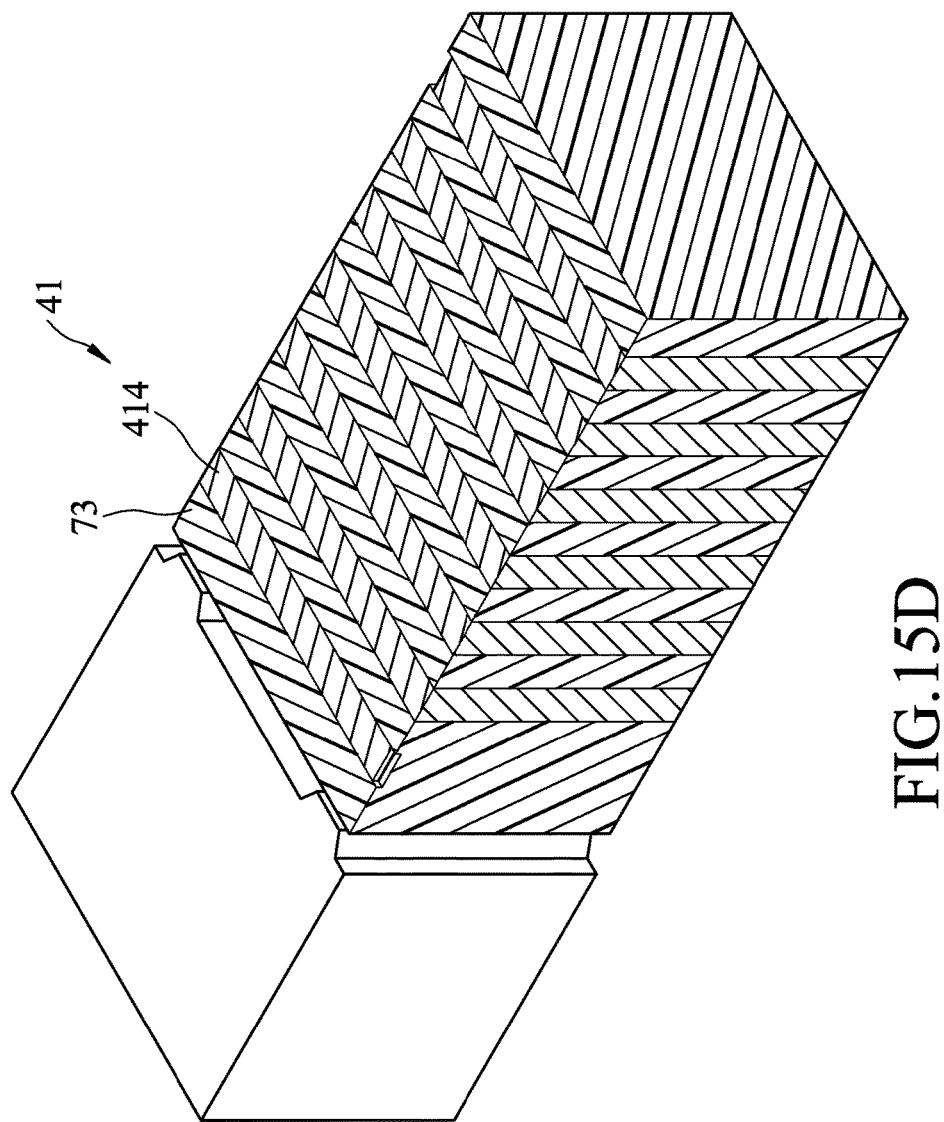


FIG. 15D

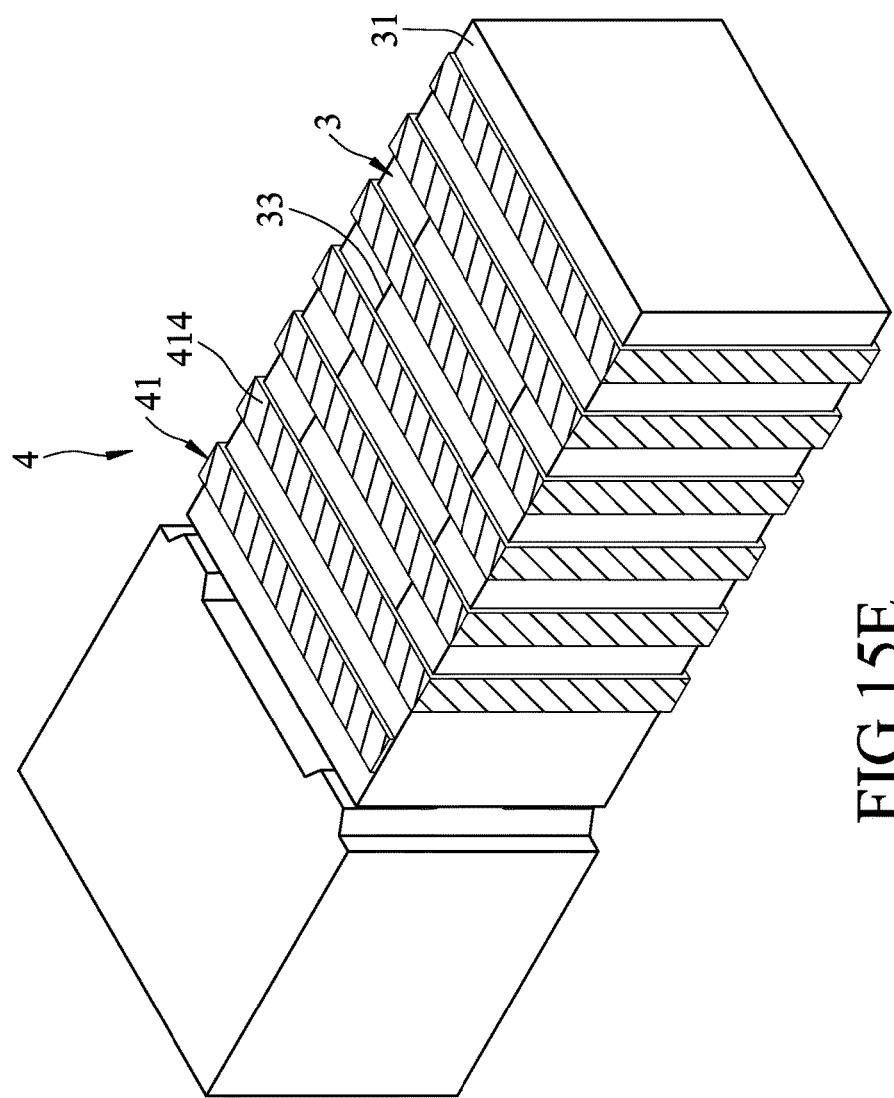


FIG. 15E

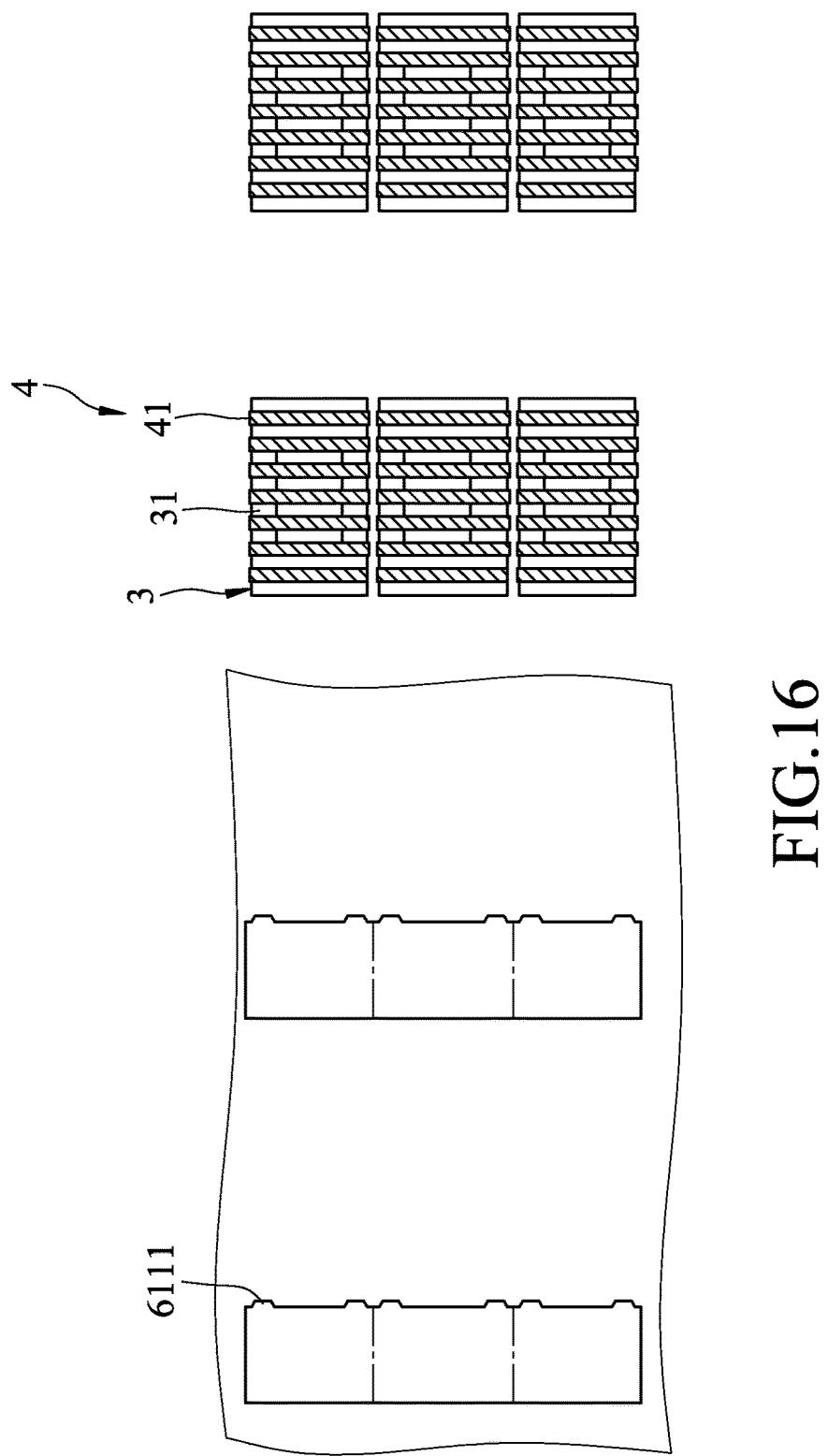
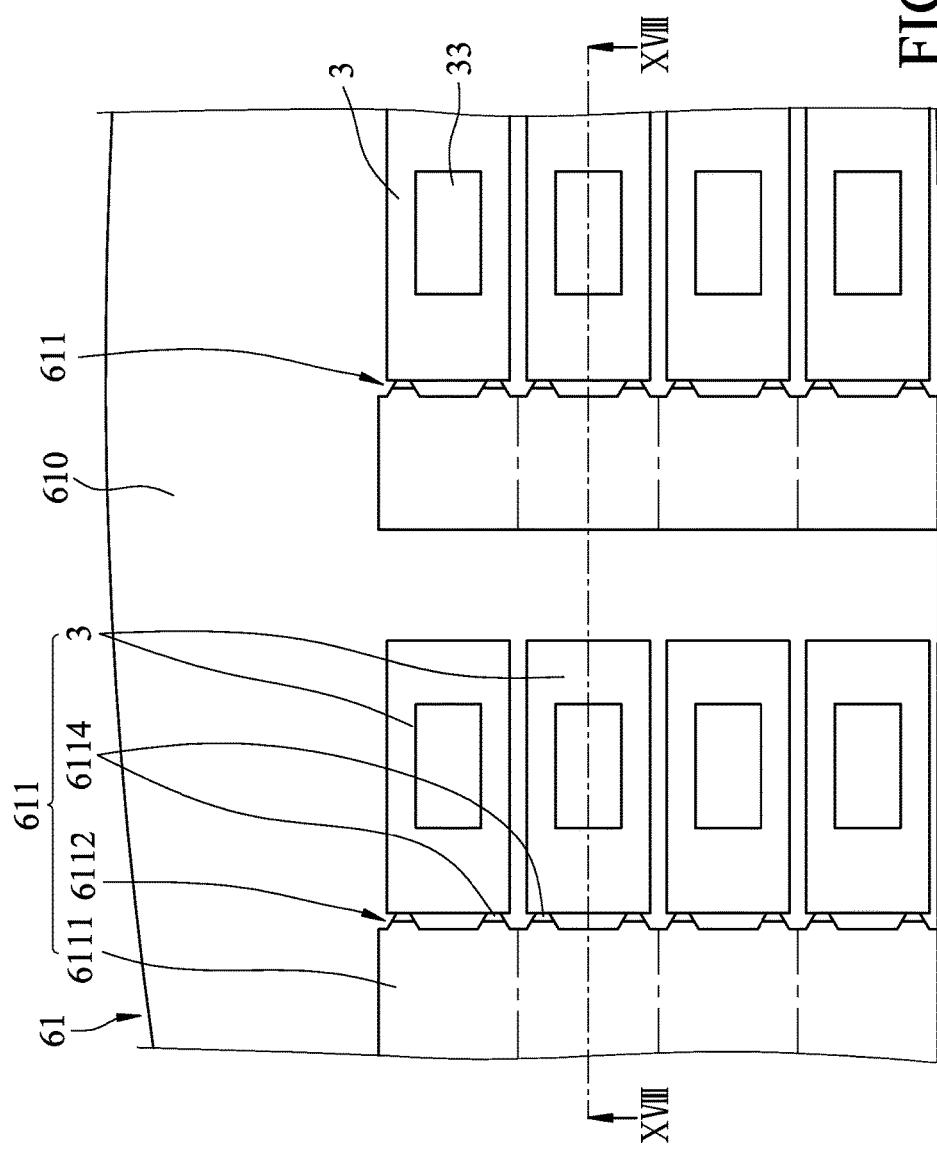


FIG. 17



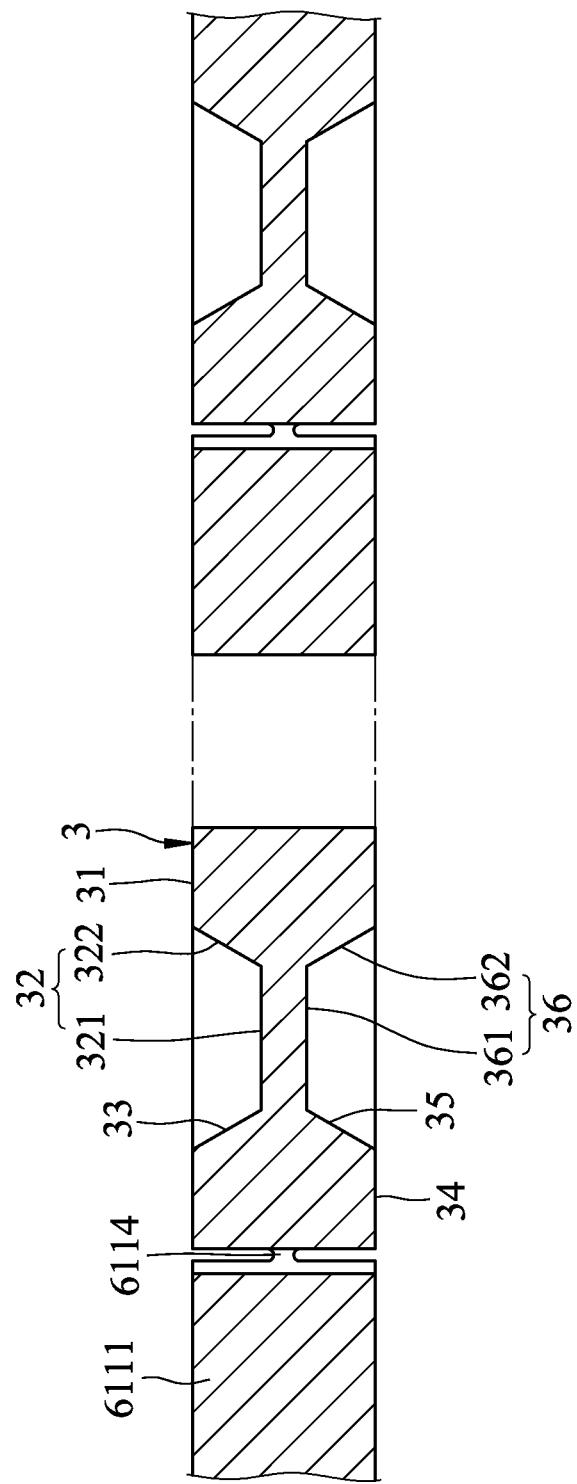


FIG. 18A

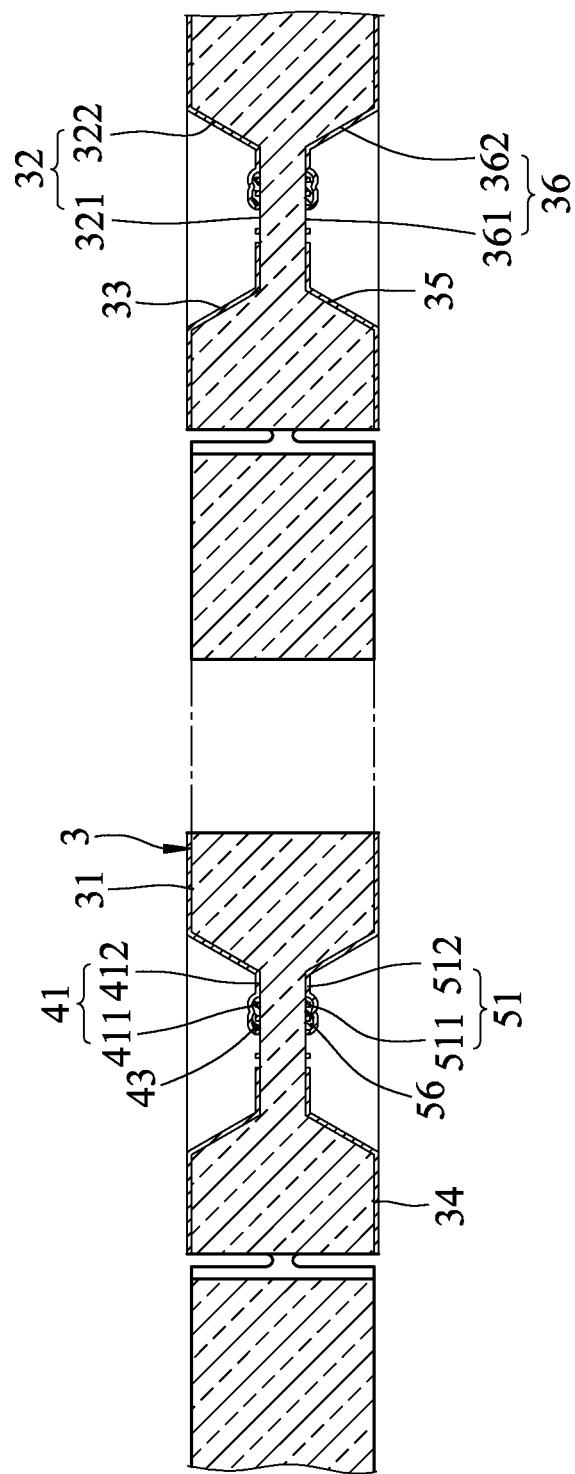


FIG. 18B

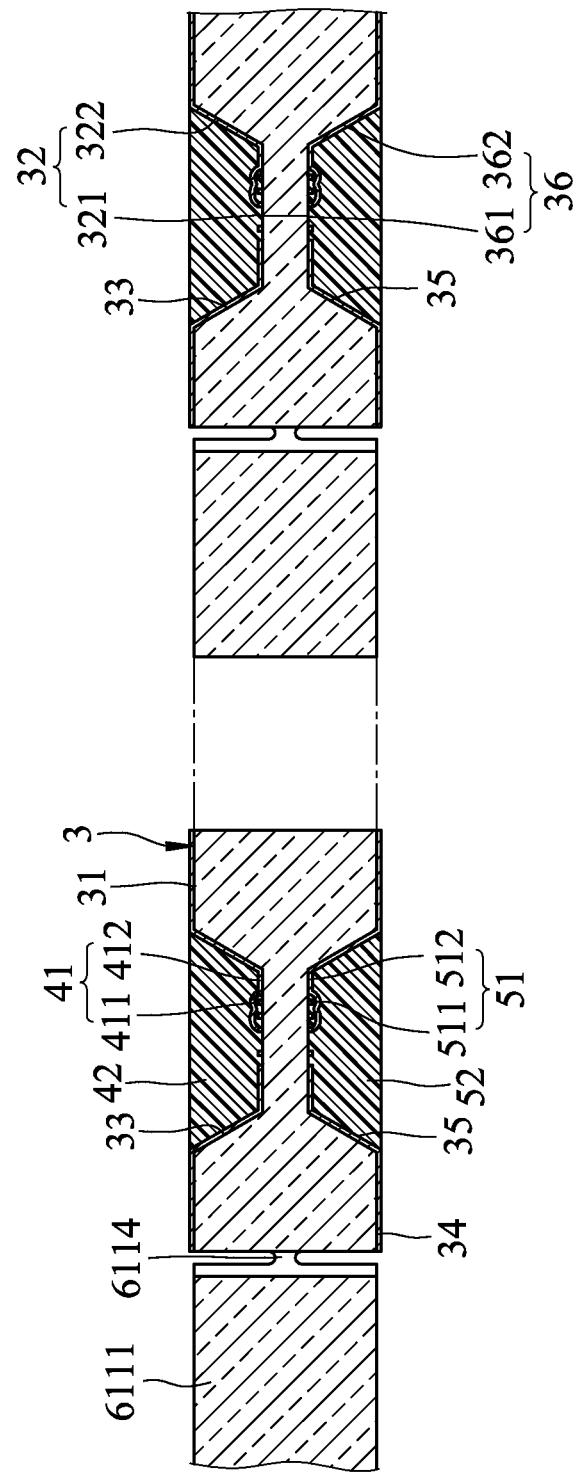


FIG. 18C

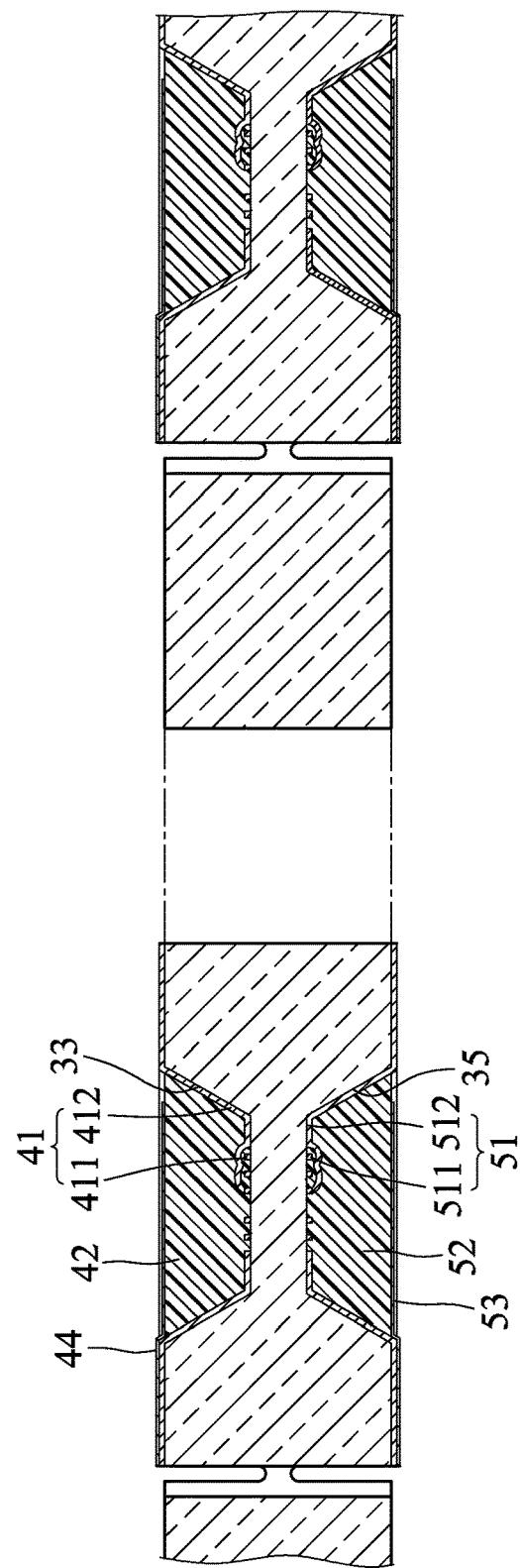


FIG. 19A

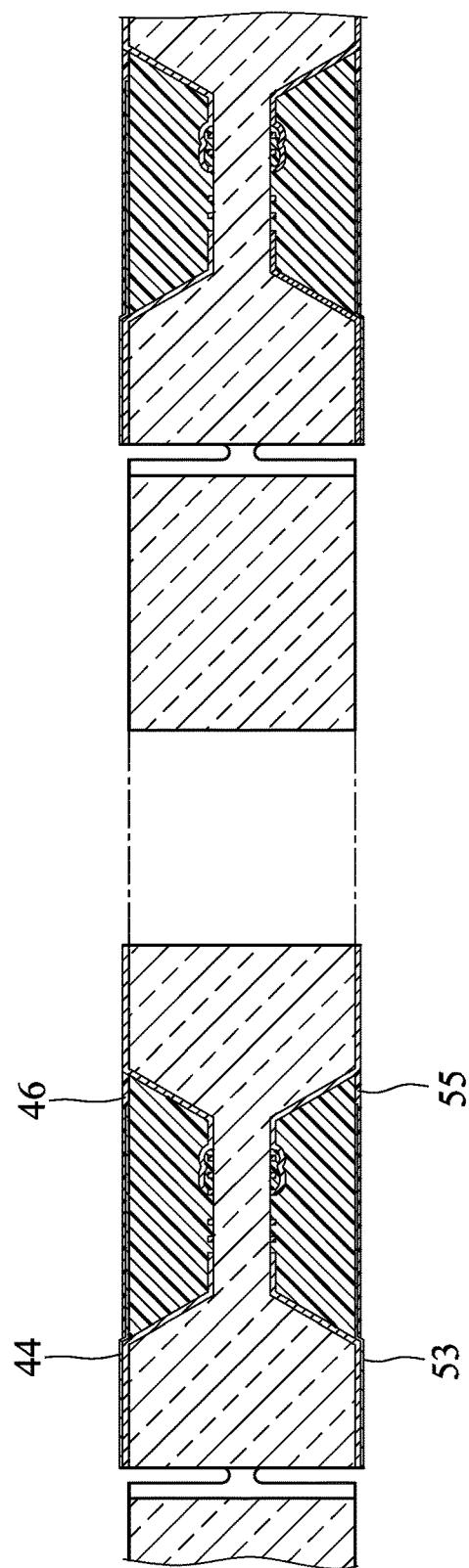


FIG. 19B

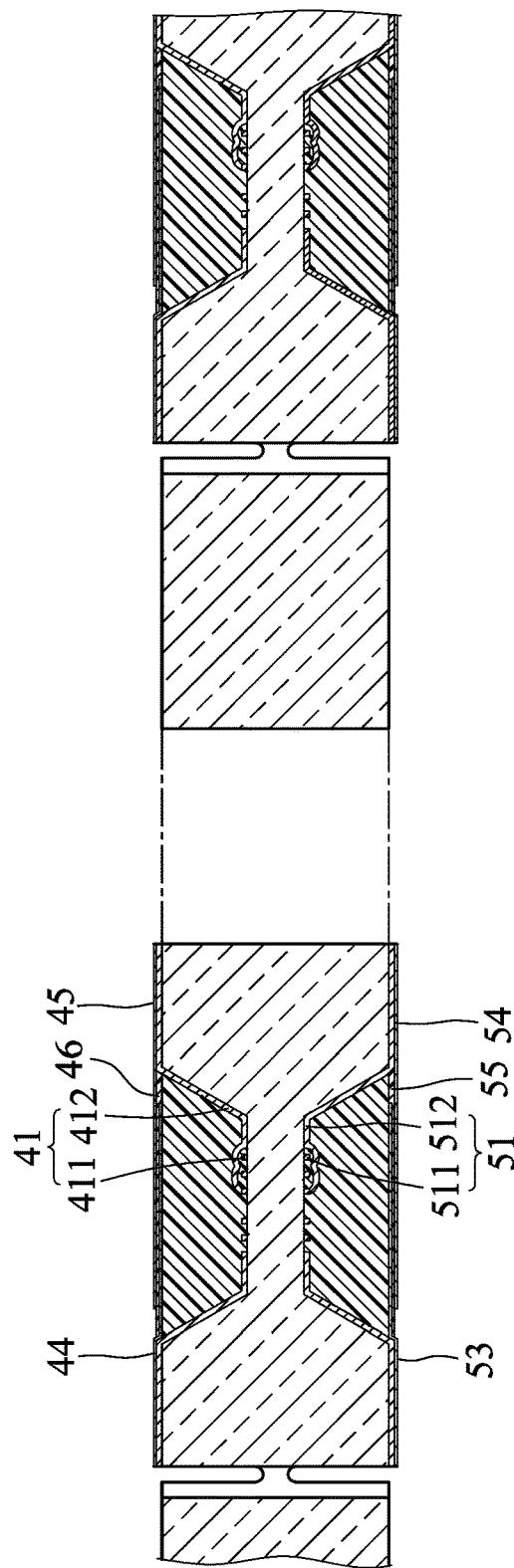


FIG. 19C

1

EMBEDDED PASSIVE CHIP DEVICE AND
METHOD OF MAKING THE SAMECROSS-REFERENCE TO RELATED
APPLICATION

This is a divisional application of U.S. patent application Ser. No. 15/152,877, filed on May 12, 2016, which claims priority to Taiwanese Patent Application No. 104120532, filed on Jun. 25, 2015, the disclosure of which is hereby incorporated by reference.

FIELD

The disclosure relates to a passive chip device and a method of making the same, more particularly to an embedded passive chip device and a method of making the same.

BACKGROUND

A passive device is referred to as a circuit device that is not capable of providing power gain. A capacitor, an inductor, and a resistor are all considered as passive devices for mainly filtering or blocking higher-frequency alternating current (AC). For example, a magnetic-core inductor that has a coil wound on a magnetic core may be used as a choke or a common mode filter, and an assembly of a magnetic-core inductor and a capacitor that are electro-connected to each other may be used as an LC filter.

There are three types of commercially available inductors, namely thin film type inductors, multilayered type inductors, and wire wound type inductors.

TW patent application publication No. 201440090 A discloses a multilayered type inductor (see FIG. 1) and a method of making the same.

The method of making the multilayered type inductor includes the steps of: laminating a first circuit plate 110, a second circuit plate 120, a third circuit plate 130 and a fourth circuit plate 140 (see FIG. 2A); attaching an assembly of a supporting film 150 and a bonding pad circuit 160 to the first circuit plate 110 (see FIG. 2B); transferring the bonding pad circuit 160 from the supporting film 150 to the first circuit plate 110 (see FIG. 2C); removing the supporting film 150 from the bonding pad circuit 160 (see FIG. 2D); sintering the first, second, third and fourth circuit plates 110, 120, 130, 140 and the bonding pad circuit 160 so as to form a multilayered circuit substrate 100 (see FIG. 2E); and scribing the multilayered circuit substrate 100 using a scribe 170 (see FIG. 2F), so that the multilayered circuit substrate 100 can be broken into a plurality of multilayered type inductors 10 (see FIG. 1).

Referring to FIG. 1, each of the first, second, third and fourth circuit plates 110, 120, 130, 140 includes a respective one of non-magnetic bodies 111, 121, 131, 141 and a respective one of first, second, third and fourth circuit patterns 112, 122, 132, 142. Formation of the first, second, third and fourth circuit plates 110, 120, 130, 140 requires numerous steps (a total of at least 13 steps), including punching each non-magnetic body 111, 121, 131, 141 to form holes, filling the conductive paste in the holes, forming the first, second, third and fourth circuit patterns 112, 122, 132, 142 and sintering before laminating the first, second, third and fourth circuit plates 110, 120, 130, 140.

The conventional method may tend to cause undesired non-ohmic contact and Joule-heating generated at the interfaces between every two adjacent ones of the first, second, third and fourth circuit patterns 112, 122, 132, 142.

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In order to prevent the undesired non-ohmic contact and Joule-heating and reduce the steps of the method of making the multilayered type inductor, TW patent No. 554355 discloses an improved chip inductor and a method of making the same.

Referring to FIGS. 3 and 4, the method of making the improved chip inductor includes the steps of: providing a ceramic substrate 200 which has a thickness of 150 μm ; laminating on the ceramic substrate 200 a first circuit layer 210 with a predetermined pattern (such as a spiral coil), a first insulator layer 220 of polyimide (PI), a second circuit layer 230 with a predetermined pattern, a second insulator layer 240 of polyimide, and a third insulator layer 250 which is made from a PI-based material containing inorganic additives, such as Co, Fe, and Mn, so as to form a semi-product; heating the first and second circuit layers 210, 230 and the first, second and third insulator layers 220, 240, 250; forming a plurality of scribing lines (not shown) with a grid pattern on the third insulator layer 250 using a laser beam; and breaking the first and second circuit layers 210, 230 and the first, second and third insulator layers 220, 240, 250 along the scribing lines using a roller so as to form a plurality of chip inductors 2. The total thickness of the first circuit layer 210 and the first insulator layer 220 is 20 μm . The total thickness of the second circuit layer 230 and the second insulator layer 240 is 20 μm . The third insulator layer 250 has a thickness ranging from 20 μm to 30 μm .

Since the size of the aforesaid chip inductor 2 is 1 mm \times 0.5 mm or 0.6 mm \times 0.3 mm, it is too big to be used in a thin and small electronic device, such as a cellular phone.

SUMMARY

Therefore, an object of the disclosure is to provide an embedded passive chip device that can alleviate at least one of the drawbacks of the prior arts.

According to the disclosure, the embedded passive chip device includes a chip body and a functional layered structure.

The chip body has a circuit-forming surface that is formed with a recess.

The functional layered structure is formed on the chip body, and includes a conductive layer that has at least a portion which covers at least partially the circuit-forming surface, and a magnetic layer that is disposed within the recess and that is inductively coupled to the conductive layer for generating inductance.

Another object of the disclosure is to provide a method of making an embedded passive chip device that can overcome the aforesaid drawbacks of the prior art.

According to the disclosure, the method of making the embedded passive chip device includes: forming a patterned wafer which has a peripheral end portion and at least one passive-component unit that includes a connecting portion, a breaking line, and a plurality of spaced apart chip bodies, the connecting portion being connected to the peripheral end portion, the breaking line having a plurality of connecting tabs that are spaced apart from one another, each of the connecting tabs being disposed between and interconnecting the connecting portion and a respective one of the chip bodies, each of the chip bodies having a circuit-forming surface that is formed with a recess; forming a functional layered structure on each of the chip bodies, the functional layered structure including a conductive layer that has at least a portion which covers at least partially the circuit-forming surface, and a magnetic layer that is disposed within the recess and that is inductively coupled to the conductive

layer for generating inductance; and breaking the patterned wafer along the breaking line by applying an external force thereto so as to form a plurality of embedded passive chip devices.

BRIEF DESCRIPTION OF THE DRAWINGS

Other features and advantages of the disclosure will become apparent in the following detailed description of the embodiments with reference to the accompanying drawings, of which:

FIG. 1 is an exploded perspective view of a multilayered type inductor disclosed in TW patent application publication No. 201440090 A;

FIGS. 2A to 2F are sectional views illustrating consecutive steps of a method of making the multilayered type inductor of FIG. 1;

FIG. 3 is a sectional view illustrating a semi-product formed by a method disclosed in TW patent No. 554355;

FIG. 4 is a sectional view illustrating inductors disclosed in TW patent No. 554355;

FIG. 5 is a schematic top view of the first embodiment of an embedded passive chip device according to the disclosure;

FIG. 6 is a sectional view taken along line VI-VI of FIG. 5;

FIG. 7 is a schematic top view of the second embodiment of the embedded passive chip device according to the disclosure;

FIG. 8 is a sectional view taken along line VIII-VIII of FIG. 7;

FIG. 9 is a schematic top view of the third embodiment of the embedded passive chip device according to the disclosure;

FIG. 10 is a sectional view taken along line X-X of FIG. 9;

FIG. 11 is an equivalent circuit of the third embodiment;

FIG. 12 is a fragmentary top view illustrating a step of a method of making the first embodiment of the embedded passive chip device according to the disclosure;

FIG. 13 is an enlarge view of an encircled portion of FIG. 12;

FIG. 14 is a sectional view taken along line XIV-XIV of FIG. 13;

FIGS. 15A to 15E are perspective views illustrating consecutive steps of the method of making the first embodiment of the embedded passive chip device according to the disclosure;

FIG. 16 is a fragmentary top view illustrating a step of a method of making the first embodiment of the embedded passive chip device according to the disclosure;

FIG. 17 is a fragmentary top view illustrating a step of a method of making the second embodiment of the embedded passive chip device according to the disclosure;

FIGS. 18A to 18C are perspective views illustrating consecutive steps of the method of making the second embodiment of the embedded passive chip device according to the disclosure; and

FIGS. 19A to 19C are perspective views illustrating consecutive steps of the method of making the third embodiment of the embedded passive chip device according to the disclosure.

DETAILED DESCRIPTION

Before the disclosure is described in greater detail, it should be noted that like elements are denoted by the same reference numerals throughout the disclosure.

Referring to FIGS. 5 and 6, the first embodiment of an embedded passive chip device includes a chip body 3 and a first functional layered structure 4.

The chip body 3 has a first circuit-forming surface 31 that is formed with a first recess 33.

The first functional layered structure 4 is formed on the chip body 3, and includes a first conductive layer 41 that has at least a portion which covers at least partially the first circuit-forming surface 31, and a first magnetic layer 42 that is disposed within the first recess 33 and that is inductively coupled to the first conductive layer 41 for generating inductance.

Preferably, the chip body 3 is made from a Si-based material or metal. Examples of the Si-based material may include quartz, silicon wafer, SiC and Si_3N_4 . The chip body 3 is in the form of a single piece, so as to have an excellent mechanical strength. The chip body 3 may be formed by etching a bulk, such as a quartz wafer or a Si wafer.

It is noted that the chip body 3 may have a size ranging from a micrometer scale to a millimeter scale. The first recess 33 has a depth (d). The chip body 3 has a thickness (t). In certain embodiments, the ratio (d/t) of the depth (d) to the thickness (t) ranges from 0.05 to 0.95 for obtaining desired properties of the first magnetic layer 42 of the first conductive layered structure 4. Preferably, the ratio (d/t) ranges from 0.35 to 0.95. More preferably, the ratio (d/t) ranges from 0.45 to 0.95.

The first conductive layer 41 is in the form of a coil, and is disposed around the chip body 3, such that the first embodiment serves as a choke.

Referring to FIGS. 7 and 8, the second embodiment of the embedded passive chip device differs from the first embodiment in the structure of the first functional layered structure 4. In this embodiment, the first recess 33 is defined by a first recess-defining surface 32 that contacts the first magnetic layer 42 and that has a base portion 321 and a surrounding portion 322 which is disposed between and interconnects the base portion 321 and the first circuit-forming surface 31. The first conductive layer 41 has a spiral part 411 and an extending part 412. The spiral part 411 is formed on the base portion 321, and contacts and is covered by the first magnetic layer 42. The extending part 412 extends from the spiral part 411, and contacts the surrounding portion 322 and the first circuit-forming surface 31. The first functional layered structure 4 further includes an insulator layer 43 that is formed on the base portion 321 and that covers a portion of the spiral part 411. The extending part 412 further extends on the insulator layer 43 for crossing over the portion of the spiral part 411.

The chip body 3 further includes a second circuit-forming surface 34. The second embodiment of the embedded chip device further includes a second functional layered structure 5.

The second circuit-forming surface 34 is opposite to the first circuit-forming surface 31, and is formed with a second recess 35. The second functional layered structure 5 is formed on the chip body 3, and includes a second conductive layer 51 extending on the second circuit-forming surface 34 and a second magnetic layer 52 that is disposed within the second recess 35 and that is inductively coupled to the second conductive layer 51 for generating inductance.

The second recess 35 is defined by a second recess-defining surface 36 that contacts the second magnetic layer 52 and that has a base portion 361 and a surrounding portion 362 which is disposed between and interconnects the base portion 361 and the second circuit-forming surface 34. The second conductive layer 51 has a spiral part 511 and an

extending part 512. The spiral part 511 of the second conductive layer 51 is formed on the base portion 361 of the second recess-defining surface 36, and contacts and is covered by the second magnetic layer 52. The extending part 512 of the second conductive layer 51 extends from the spiral part 511 of the second conductive layer 51, and contacts the surrounding portion 362 of the second recess-defining surface 36 and the second circuit-forming surface 34. The second functional layered structure 5 further includes an insulator layer 56 that is formed on the base portion 361 of the second recess-defining surface 36 and that covers a portion of the spiral part 511 of the second conductive layer 51. The extending part 512 of the second conductive layer 51 further extends on the insulator layer 56 of the second functional layered structure 5 for crossing over the portion of the spiral part 511 of the second conductive layer 51.

In the second embodiment, the first and second recesses 33, 35 are symmetrical to each other, and the first and second functional layered structures 4, 5 are symmetrical to each other, such that the second embodiment serves as a common mode filter.

Referring to FIGS. 9 and 10, the third embodiment differs from the second embodiment in that the first functional layered structure 4 further includes first and second electrode layers 44, 45 and a first dielectric layer 46. The second functional layered structure 5 further includes third and forth electrode layers 53, 54, and a second dielectric layer 55.

The first and second electrode layers 44, 45 are disposed on the first magnetic layer 42. The first dielectric layer 46 is disposed between the first and second electrode layers 44, 45. The first and second electrode layers 44, 45 and the first dielectric layer 46 cooperatively define a first capacitor. The extending part 412 of the first conductive layer 41 is electro-connected to the first and second electrode layers 44, 45.

The third and fourth electrode layers 53, 54 are disposed on the second magnetic layer 52. The second dielectric layer 55 is disposed between the third and fourth electrode layers 53, 54. The third and fourth electrode layers 53, 54 and the second dielectric layer 55 cooperatively define a second capacitor. The extending part 512 of the second conductive layer 51 is electro-connected to the third and fourth electrode layers 53, 54.

In this embodiment, the first and second functional layered structures 4, 5 are symmetrical to each other, such that the third embodiment may serve as an LC filter.

FIG. 11 illustrates an equivalent circuit of the third embodiment. It shows that each of the first and second functional layered structures 4, 5 (see FIG. 10) forms a capacitor and an inductor which are in parallel connection.

The following description illustrates a method of making the embedded chip device of the first embodiment of the disclosure, and should not be construed as limiting the scope of the disclosure. The method includes the steps of S1 to S3.

Referring to FIGS. 12 to 14, in step S1, two first patterned photoresist layers (not shown) are respectively formed on top and bottom surfaces (not shown) of a wafer (not shown), such that each of the top and bottom surfaces of the wafer has wider exposed regions and narrow exposed regions (not shown) which are exposed from the respective first patterned photoresist layer. The narrow exposed regions have an etching rate less than those of the wider exposed regions. The wafer is subsequently patterned using an etching process so as to form a patterned wafer 61. The patterned wafer 61 has a peripheral end portion 610, and at least one passive-component unit 611 that includes a connecting por-

tion 6111, a breaking line 6112, and a plurality of the chip bodies 3 that are spaced apart from one another. The connecting portion 6111 is connected to the peripheral end portion 610. The breaking line 6112 has a plurality of connecting tabs 6114 that are spaced apart from one another and that correspond in position to respective ones of the narrow exposed regions of the wafer. Each of the connecting tabs 6114 is disposed between and interconnects the connecting portion 6111 and a respective one of the chip bodies 3.

Each of the chip bodies 3 has a structure as shown in FIG. 6.

In certain embodiments, the wafer may be made from quartz. A metal protecting film (not shown) is needed to be formed on each of the wafer at least at a portion where the chip bodies 3 are to be formed before forming the patterned wafer 61, so as to prevent the chip bodies 3 from being damaged.

In this embodiment, each of the connecting tabs 6114 is reduced in width from the connecting portion 6111 toward the respective one of the chip bodies 3. Each of the connecting tabs 6114 has a thickness less than that of the connecting portion 6111 and that of the chip bodies 3. In certain embodiment, the thickness of the connecting tabs 6114 may be further reduced by a scribe.

In step S2 (see FIGS. 15A to 15E) the first functional layered structure 4 is formed on each of the chip bodies 3.

In this embodiment, the forming process of the first functional layered structure 3 in step S2 includes sub-steps of S21 to S25.

In sub-step S21 (see FIG. 15A), a magnetic ceramic powder is compounded with an organic solvent and a binder, so as to form a magnetic ceramic green which is in the form of a paste. The magnetic ceramic green is disposed in and fills the first recess 33 and is subsequently cured, such that the organic solvent is volatilized and the binder is solidified, so as to form the first magnetic layer 42 which is disposed within the recess 33 and which is bonded to the recess-defining surface (not shown). The magnetic ceramic powder may be made from Fe_3O_4 with an inverse spinel structure.

In sub-step S22 (see FIG. 15B), a seed layer 413 is formed on each of the chip bodies 3 and the corresponding first magnetic layer 42.

In sub-step S23 (see FIG. 15C), a second patterned photoresist layer 73 is formed on the seed layer 413, such that the seed layer 413 has an exposed region 415 that is exposed from the second patterned photoresist layer 73, and a covered region 416 that is covered with the second patterned photoresist layer 73.

In sub-step S24 (see FIG. 15D), a metal layer 414 is electroplated on the exposed region 415 of the seed layer 413 so as to form the first conductive layer 41 on and around each of the chip bodies 3 of the patterned wafer 61.

In sub-step S25 (see FIG. 15E), the second patterned photoresist layer 73 and the covered region 416 of the seed layer 413 are removed from the patterned wafer 61.

Preferably, the seed layer 413 may be made from a catalytically active material selected from the group consisting of Pt, Pd, Au, Ag and Cu, or a conductive material.

When the seed layer 413 is made from the catalytically active material, the metal layer 414 is formed through chemical plating (or electroless plating) techniques. When the seed layer 413 is made from the conductive material, the metal layer 414 is formed through electro-plating techniques. In the embodiment, the seed layer 413 is deposited on each of the chip bodies 3 through electro-plating techniques.

In certain embodiments, a protecting layer (not shown) may be formed on the first conductive layer 41 after the formation of the first conductive layer 41, so as to isolate the first conductive layer 41 from atmospheric moisture or oxygen.

The first magnetic layer 42 may be made from magnetic metal powders, such as Fe, Co or Ni, instead of the magnetic ceramic powder. When the first magnetic layer 42 is made from the magnetic metal powder, an isolation layer (not shown) is needed to be formed on the first magnetic layer 42 before the formation of the first conductive layer 41 so as to prevent the first functional layered structure 4 from short circuit.

In step S3 (see FIG. 16), the patterned wafer 61 is broken along the breaking line 6112 by applying an external force thereto so as to form a plurality of embedded passive chip devices.

Referring to FIGS. 17 to 18(C), the method of making the embedded passive chip device of the second embodiment differs from the method of making the first embodiment in the formation of the first functional layered structure 4. In addition, the method further includes forming the second functional layered structure 5.

In this embodiment, the first and second functional layered structures 4, 5 are formed by the following steps.

As shown in FIGS. 17 and 18A, the wafer (not shown) is patterned using etching techniques, such that each of the chip bodies 3 of the patterned wafer 61 is formed with the first and second recess 33, 35.

As shown in FIG. 18B, the first and the second conductive layers 41, 51 are respectively formed on the first and second recess-defining surfaces 32, 36 through deposition techniques.

As shown in FIG. 18C, the first and second magnetic layers 42, 52 are respectively formed on the first and the second conductive layers 41, 51 such that the same are embedded in the first and second recesses 33, 35.

Referring to FIGS. 19A to 19C, the method of making the embedded passive chip device of the third embodiment differs from the method of making the second embodiment in that, after forming the first and second magnetic layers 42, 52, the first and second capacitors are subsequently formed.

As shown in FIG. 19A, the first electrode layer 44 and the third electrode layer 53 are respectively formed on the first and second magnetic layers 42, 52 through deposition techniques.

As shown in FIG. 19B, the first and second dielectric layers 46, 55 are respectively formed on the first electrode layer 44 and the third electrode layer 53.

As shown in FIG. 19C, the second electrode layer 45 and the forth electrode layer 54 are respectively formed on the first and second dielectric layers 46, 55 through deposition techniques.

In summary, the method of making the embedded passive chip device of the present disclosure may be advantageous over the prior art in reducing the steps of making the passive device.

Furthermore, the chip body 3 of the embedded passive chip device of the present disclosure is in the form of a single piece. As such, the chip body 3 of the embedded passive chip device of the present disclosure has a higher mechanical strength than that of the conventional multilayered type passive device. In addition, the size of the embedded passive

chip device of the present disclosure can range from hundreds of micrometers to hundreds of millimeters.

While the disclosure has been described in connection with what are considered the exemplary embodiments, it is understood that this disclosure is not limited to the disclosed embodiments but is intended to cover various arrangements included within the spirit and scope of the broadest interpretation so as to encompass all such modifications and equivalent arrangements.

What is claimed is:

1. An embedded passive chip device comprising:
a chip body having a first circuit-forming surface that is formed with a first recess; and
a first functional layered structure formed on said chip body and including a first conductive layer that has at least a portion which covers at least partially said first circuit-forming surface, and a first magnetic layer that is disposed within said first recess and that is inductively coupled to said first conductive layer for generating inductance,
wherein said first recess is defined by a recess-defining surface that contacts said first magnetic layer and that has a base portion and a surrounding portion which is disposed between and interconnects said base portion and said first circuit-forming surface, said first conductive layer having a spiral part that is formed on said base portion and that contacts and is covered by said first magnetic layer, and an extending part that extends from said spiral part and that further extends on and contacts said surrounding portion and said first circuit-forming surface.

2. The embedded passive chip device of claim 1, wherein said chip body is made from a Si-based material or metal.

3. The embedded passive chip device of claim 1, wherein said first functional layered structure further includes an insulator layer that is formed on said base portion and that covers a portion of said spiral part, said extending part further extending on said insulator layer.

4. The embedded passive chip device of claim 3, wherein said first functional layered structure further includes first and second electrode layers disposed on said first magnetic layer, and
a dielectric layer disposed between said first and second electrode layers;
wherein said first and second electrode layers and said dielectric layer cooperatively define a capacitor;
wherein said extending part is electro-connected to at least one of said first and second electrode layers.

5. The embedded passive chip device of claim 1, wherein said chip body further has a second circuit-forming surface that is opposite to said first circuit-forming surface and that is formed with a second recess, said embedded passive chip device further comprising a second functional layered structure that is formed on said chip body and that includes a second conductive layer extending on said second circuit-forming surface, and a second magnetic layer embedded in said second recess and inductively coupled to said second conductive layer for generating inductance.

6. The embedded passive chip device of claim 5, wherein said first and second functional layered structures are symmetrical to each other.